

Silicon PNP Power Transistor

2SA1060

DESCRIPTION

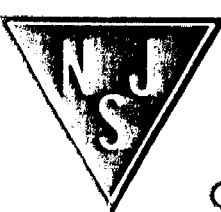
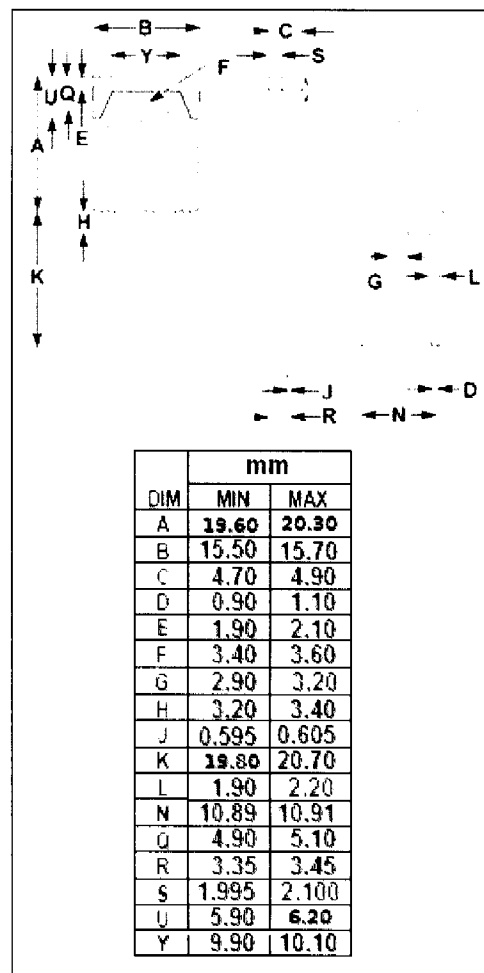
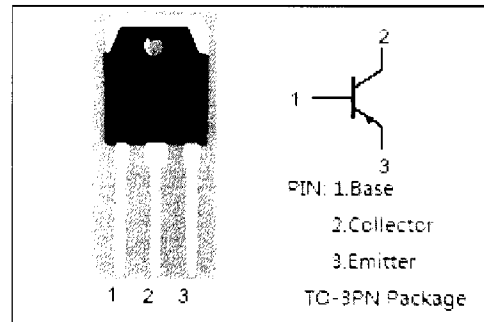
- Collector-Emitter Breakdown Voltage-
 $V_{(BR)CEO} = -80V(\text{Min})$
- High Power Dissipation
- Complement to Type 2SC2484

APPLICATIONS

- Designed for high power audio frequency amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|---------|------------------|
| V_{CBO} | Collector-Base Voltage | -80 | V |
| V_{CEO} | Collector-Emitter Voltage | -80 | V |
| V_{EBO} | Emitter-Base Voltage | -5 | V |
| I_C | Collector Current-Continuous | -5 | A |
| I_{CM} | Collector Current-Peak | -8 | A |
| P_C | Collector Power Dissipation @ $T_C=25^\circ\text{C}$ | 60 | W |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | -55~150 | $^\circ\text{C}$ |



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Quality Semi-Conductors

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ELECTRICAL CHARACTERISTICS

$T_c=25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|---------------|--------------------------------------|---|-----|------|------|---------------|
| $V_{(BR)CEO}$ | Collector-Emitter Breakdown Voltage | $I_C = -30\text{mA}$; $I_B = 0$ | -80 | | | V |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = -3\text{A}$; $I_B = -0.3\text{A}$ | | | -2.0 | V |
| $V_{BE(on)}$ | Base-Emitter On Voltage | $I_C = -3\text{A}$; $V_{CE} = -5\text{V}$ | | | -1.8 | V |
| I_{CBO} | Collector Cutoff Current | $V_{CB} = -80\text{V}$; $I_E = 0$ | | | -50 | μA |
| I_{EBO} | Emitter Cutoff Current | $V_{EB} = -3\text{V}$; $I_C = 0$ | | | -50 | μA |
| h_{FE-1} | DC Current Gain | $I_C = -0.02\text{A}$; $V_{CE} = -5\text{V}$ | 20 | | | |
| h_{FE-2} | DC Current Gain | $I_C = -1\text{A}$; $V_{CE} = -5\text{V}$ | 40 | | 200 | |
| h_{FE-3} | DC Current Gain | $I_C = -3\text{A}$; $V_{CE} = -5\text{V}$ | 20 | | | |
| f_T | Current-Gain—Bandwidth Product | $I_C = -0.5\text{A}$; $V_{CE} = -5\text{V}$ | | 20 | | MHz |

◆ h_{FE-2} Classifications

| R | Q | P |
|-------|--------|---------|
| 40-80 | 60-120 | 100-200 |